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Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8358evvagdga

- DRAM chip configurations from 64 Mbits to 1 Gigabit with $\times 8/\times 16$ data ports
- Full ECC support (when the MPC8360E is configured as 2×32 -bit DDR memory controllers, both support ECC)
- Page mode support (up to 16 simultaneous open pages for DDR1, up to 32 simultaneous open pages for DDR2)
- Contiguous or discontinuous memory mapping
- Read-modify-write support
- Sleep mode support for self refresh SDRAM
- Supports auto refreshing
- Supports source clock mode
- On-the-fly power management using CKE
- Registered DIMM support
- 2.5-V SSTL2 compatible I/O for DDR1, 1.8-V SSTL2 compatible I/O for DDR2
- External driver impedance calibration
- On-die termination (ODT)
- PCI interface
 - PCI Specification Revision 2.3 compatible
 - Data bus widths:
 - Single 32-bit data PCI interface that operates at up to 66 MHz
 - PCI 3.3-V compatible (not 5-V compatible)
 - PCI host bridge capabilities on both interfaces
 - PCI agent mode supported on PCI interface
 - Support for PCI-to-memory and memory-to-PCI streaming
 - Memory prefetching of PCI read accesses and support for delayed read transactions
 - Support for posting of processor-to-PCI and PCI-to-memory writes
 - On-chip arbitration, supporting five masters on PCI
 - Support for accesses to all PCI address spaces
 - Parity support
 - Selectable hardware-enforced coherency
 - Address translation units for address mapping between host and peripheral
 - Dual address cycle supported when the device is the target
 - Internal configuration registers accessible from PCI
- Local bus controller (LBC)
 - Multiplexed 32-bit address and data operating at up to 133 MHz
 - Eight chip selects support eight external slaves
 - Up to eight-beat burst transfers
 - 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller
 - Three protocol engines available on a per chip select basis:
 - General-purpose chip select machine (GPCM)
 - Three user programmable machines (UPMs)
 - Dedicated single data rate SDRAM controller
 - Parity support
 - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Programmable interrupt controller (PIC)
 - Functional and programming compatibility with the MPC8260 interrupt controller
 - Support for 8 external and 35 internal discrete interrupt sources
 - Support for one external (optional) and seven internal machine checkstop interrupt sources

This table shows the estimated typical I/O power dissipation for the device.

Table 6. Estimated Typical I/O Power Dissipation

Interface	Parameter	GV _{DD} (1.8 V)	GV _{DD} (2.5 V)	OV _{DD} (3.3 V)	LV _{DD} (3.3 V)	LV _{DD} (2.5 V)	Unit	Comments
DDR I/O 65% utilization R _s = 20 Ω R _t = 50 Ω 2 pairs of clocks	200 MHz, 1 × 32 bits	0.3	0.46	—	—	—	W	—
	200 MHz, 1 × 64 bits	0.4	0.58	—	—	—	W	—
	200 MHz, 2 × 32 bits	0.6	0.92	—	—	—	W	—
	266 MHz, 1 × 32 bits	0.35	0.56	—	—	—	W	—
	266 MHz, 1 × 64 bits	0.46	0.7	—	—	—	W	—
	266 MHz, 2 × 32 bits	0.7	1.11	—	—	—	W	—
	333 MHz, 1 × 32 bits	0.4	0.65	—	—	—	W	—
	333 MHz, 1 × 64 bits	0.53	0.82	—	—	—	W	—
	333 MHz, 2 × 32 bits	0.81	1.3	—	—	—	W	—
Local Bus I/O Load = 25 pF 3 pairs of clocks	133 MHz, 32 bits	—	—	0.22	—	—	W	—
	83 MHz, 32 bits	—	—	0.14	—	—	W	—
	66 MHz, 32 bits	—	—	0.12	—	—	W	—
	50 MHz, 32 bits	—	—	0.09	—	—	W	—
PCI I/O Load = 30 pF	33 MHz, 32 bits	—	—	0.05	—	—	W	—
	66 MHz, 32 bits	—	—	0.07	—	—	W	—
10/100/1000 Ethernet I/O Load = 20 pF	MII or RMII	—	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	—	0.04	—	W	
	RGMII or RTBI	—	—	—	—	0.04	W	
Other I/O	—	—	—	0.1	—	—	W	—

4 Clock Input Timing

This section provides the clock input DC and AC electrical characteristics for the MPC8360E/58E.

NOTE

The rise/fall time on QUICC Engine block input pins should not exceed 5 ns. This should be enforced especially on clock signals. Rise time refers to signal transitions from 10% to 90% of V_{DD}; fall time refers to transitions from 90% to 10% of V_{DD}.

6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 14. DDR2 SDRAM DC Electrical Characteristics for $GV_{DD}(\text{typ}) = 1.8 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	—	± 10	μA	4
Output high current ($V_{OUT} = 1.420 \text{ V}$)	I_{OH}	-13.4	—	mA	—
Output low current ($V_{OUT} = 0.280 \text{ V}$)	I_{OL}	13.4	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	± 10	μA	—
Input current ($0 \text{ V} \leq V_{IN} \leq OV_{DD}$)	I_{IN}	—	± 10	μA	—

Notes:

- GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
- MV_{REF} is expected to equal $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} cannot exceed $\pm 2\%$ of the DC value.
- V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal MV_{REF} . This rail should track variations in the DC level of MV_{REF} .
- Output leakage is measured with all outputs disabled, $0 \text{ V} \leq V_{OUT} \leq GV_{DD}$.

This table provides the DDR2 capacitance when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 15. DDR2 SDRAM Capacitance for $GV_{DD}(\text{typ})=1.8 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:

- This parameter is sampled. $GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$, $f = 1 \text{ MHz}$, $T_A = 25^\circ\text{C}$, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the recommended operating conditions for the DDR SDRAM component(s) of the device when $GV_{DD}(\text{typ}) = 2.5 \text{ V}$.

Table 16. DDR SDRAM DC Electrical Characteristics for $GV_{DD}(\text{typ}) = 2.5 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3

This figure provides the AC test load for the DDR bus.

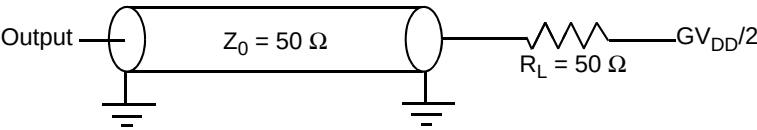


Figure 8. DDR AC Test Load

Table 22. DDR and DDR2 SDRAM Measurement Conditions

Symbol	DDR	DDR2	Unit	Notes
V_{TH}	$MV_{REF} \pm 0.31\text{ V}$	$MV_{REF} \pm 0.25\text{ V}$	V	1
V_{OUT}	$0.5 \times GV_{DD}$	$0.5 \times GV_{DD}$	V	2

Notes:

1. Data input threshold measurement point.
2. Data output measurement point.

This figure shows the DDR SDRAM output timing diagram for source synchronous mode.

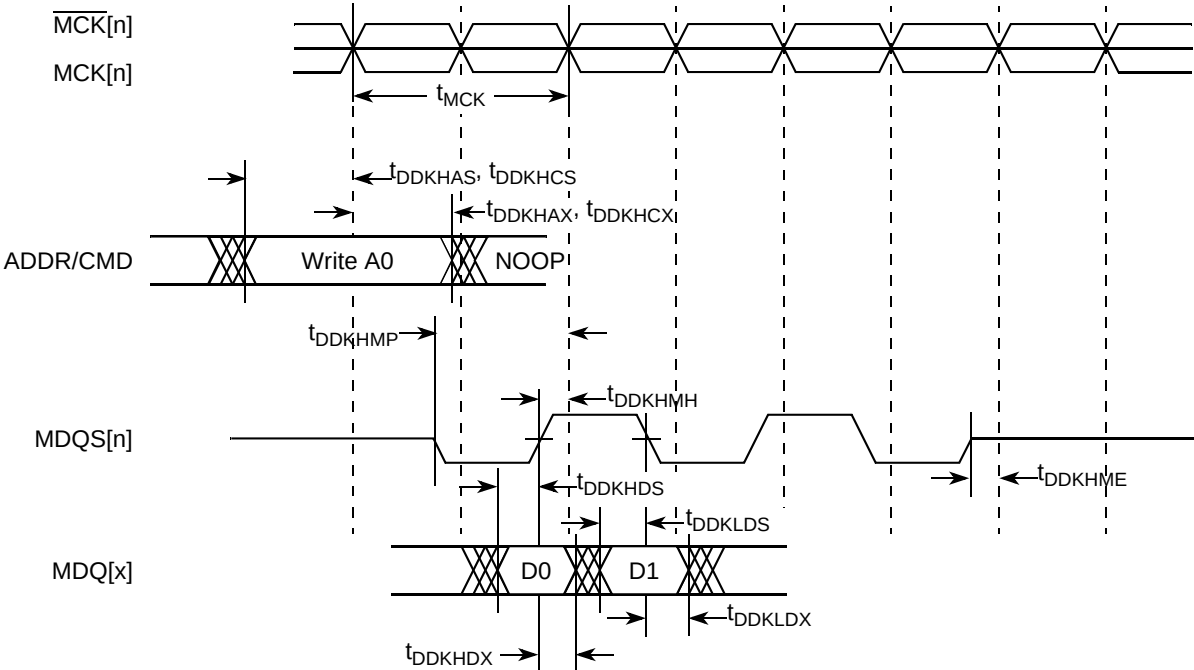


Figure 9. DDR SDRAM Output Timing Diagram for Source Synchronous Mode

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8360E/58E.

7.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface of the device.

Table 23. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V_{IH}	2	$OV_{DD} + 0.3$	V	—
Low-level input voltage OV_{DD}	V_{IL}	-0.3	0.8	V	—
High-level output voltage, $I_{OH} = -100 \mu A$	V_{OH}	$OV_{DD} - 0.4$	—	V	—
Low-level output voltage, $I_{OL} = 100 \mu A$	V_{OL}	—	0.2	V	—
Input current ($0 V \leq V_{IN} \leq OV_{DD}$)	I_{IN}	—	± 10	μA	1

Note:

- Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in [Table 1](#) and [Table 2](#).

7.2 DUART AC Electrical Specifications

This table provides the AC timing parameters for the DUART interface of the device.

Table 24. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	256	baud	—
Maximum baud rate	>1,000,000	baud	1
Oversample rate	16	—	2

Notes:

- Actual attainable baud rate is limited by the latency of interrupt processing.
- The middle of a start bit is detected as the eighth sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each sixteenth sample.

8 UCC Ethernet Controller: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speed, 10/100/1000, and MII management.

8.1 Three-Speed Ethernet Controller (10/100/1000 Mbps)—GMII/MII/RMII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to all GMII (gigabit media independent interface), MII (media independent interface), RMII (reduced media independent interface), TBI (ten-bit interface), RGMII (reduced gigabit media independent interface), and RTBI (reduced ten-bit interface) signals except MDIO (management data input/output) and MDC (management data clock). The MII, RMII, GMII, and TBI interfaces are only defined for 3.3 V, while the RGMII and RTBI interfaces are only defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard reduced pin-count interface for Gigabit Ethernet

8.2.2.2 MII Receive AC Timing Specifications

This table provides the MII receive AC timing specifications.

Table 30. MII Receive AC Timing Specifications

At recommended operating conditions with V_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise time, (20% to 80%)	t_{MRXR}	1.0	—	4.0	ns
RX_CLK clock fall time, (80% to 20%)	t_{MRXF}	1.0	—	4.0	ns

Note:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure provides the AC test load.

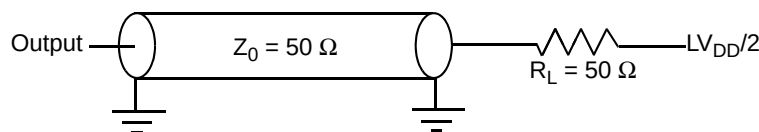


Figure 13. AC Test Load

This figure shows the MII receive AC timing diagram.

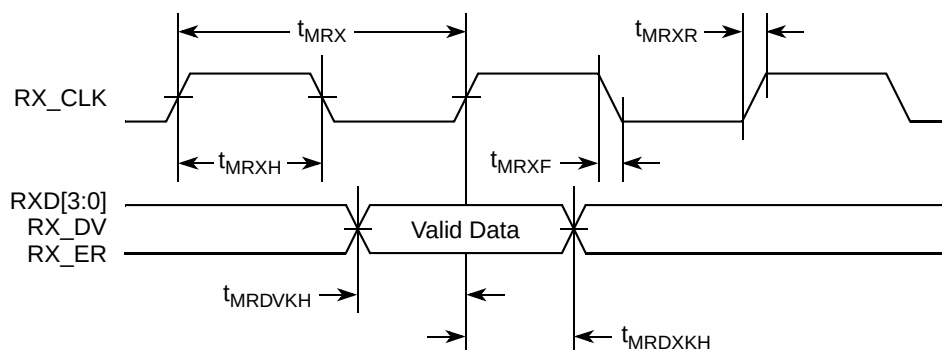


Figure 14. MII Receive AC Timing Diagram

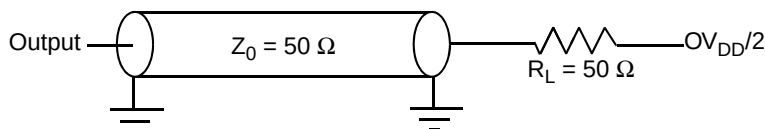
Table 41. Local Bus General Timing Parameters—DLL Bypass Mode⁹ (continued)

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus clock to output valid	t_{LBKHOV}	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	8

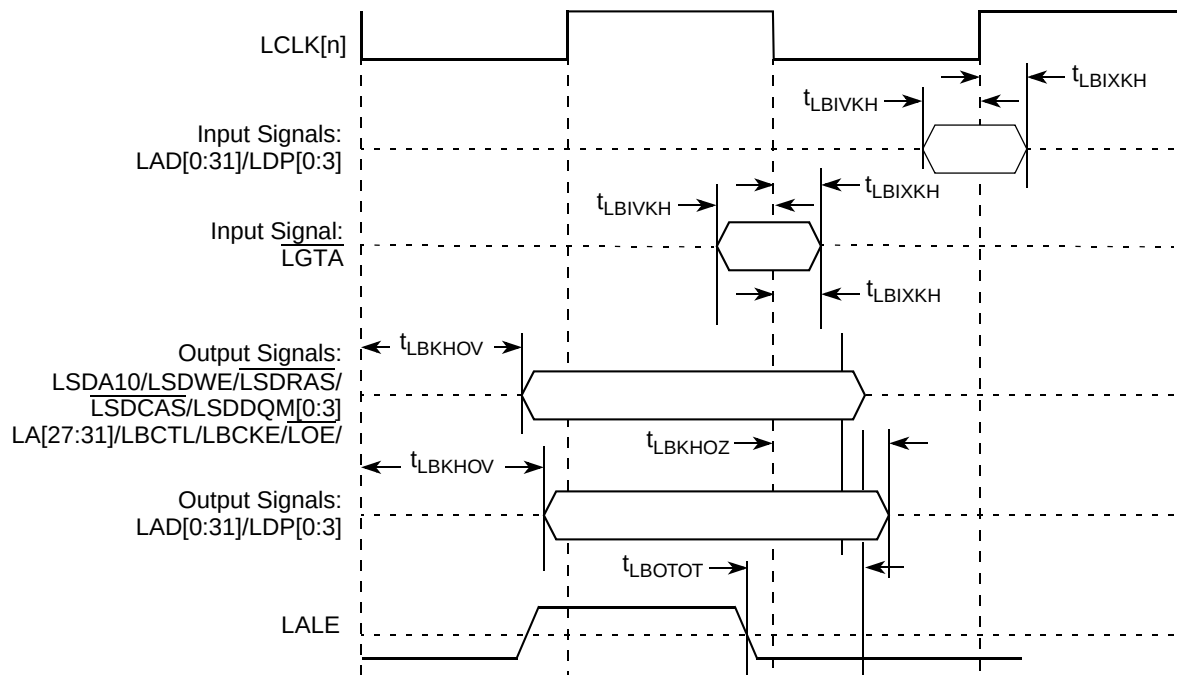
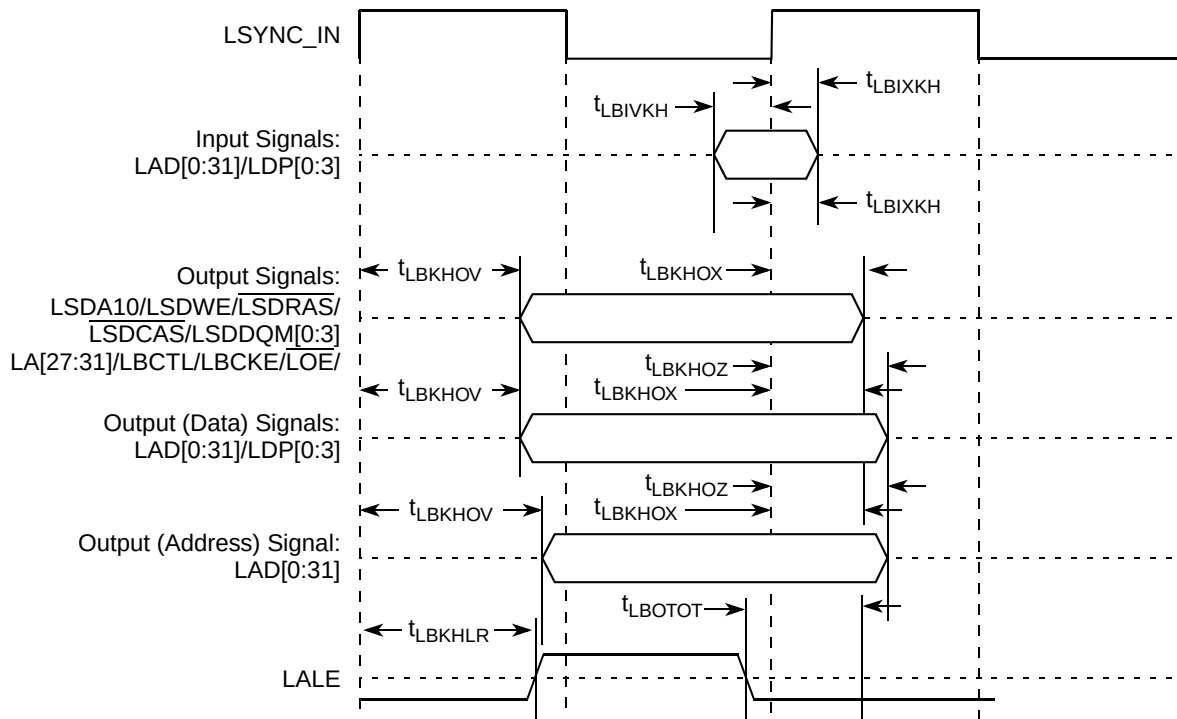
Notes:

1. The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHGX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to falling edge of LCLK0 (for all outputs and for $\overline{LGTA}$ and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and when the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

This figure provides the AC test load for the local bus.


Figure 22. Local Bus C Test Load

These figures show the local bus signals.



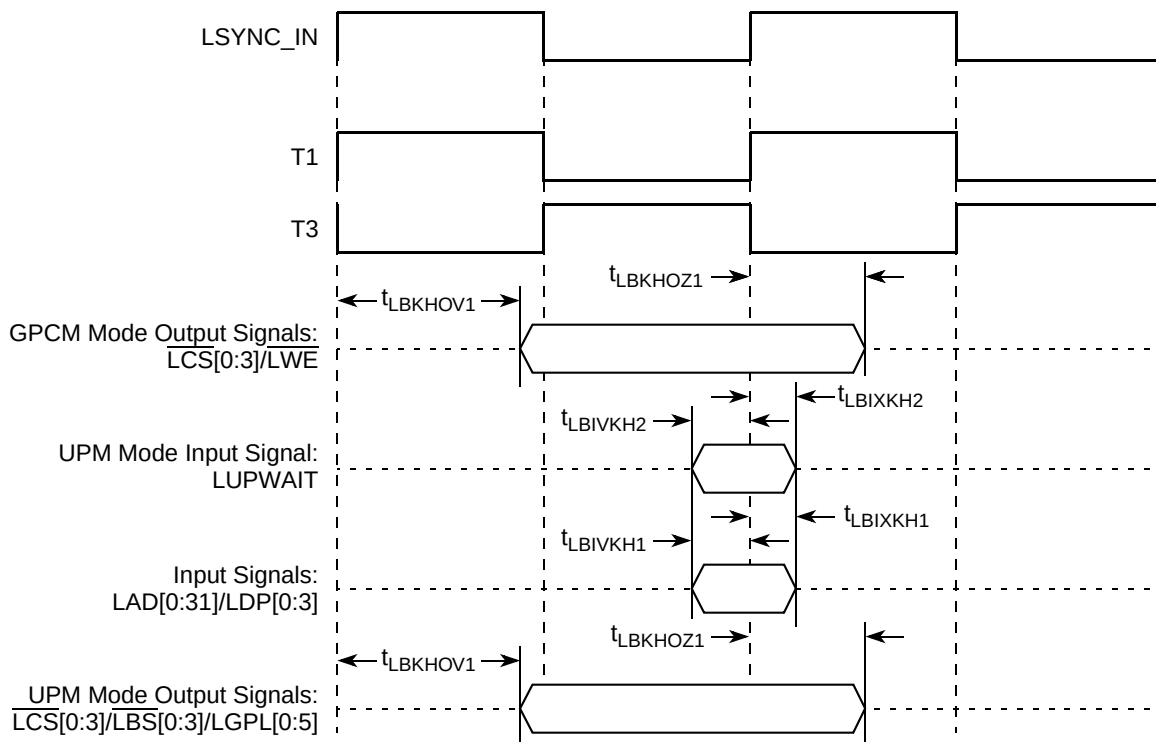


Figure 25. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Enabled)

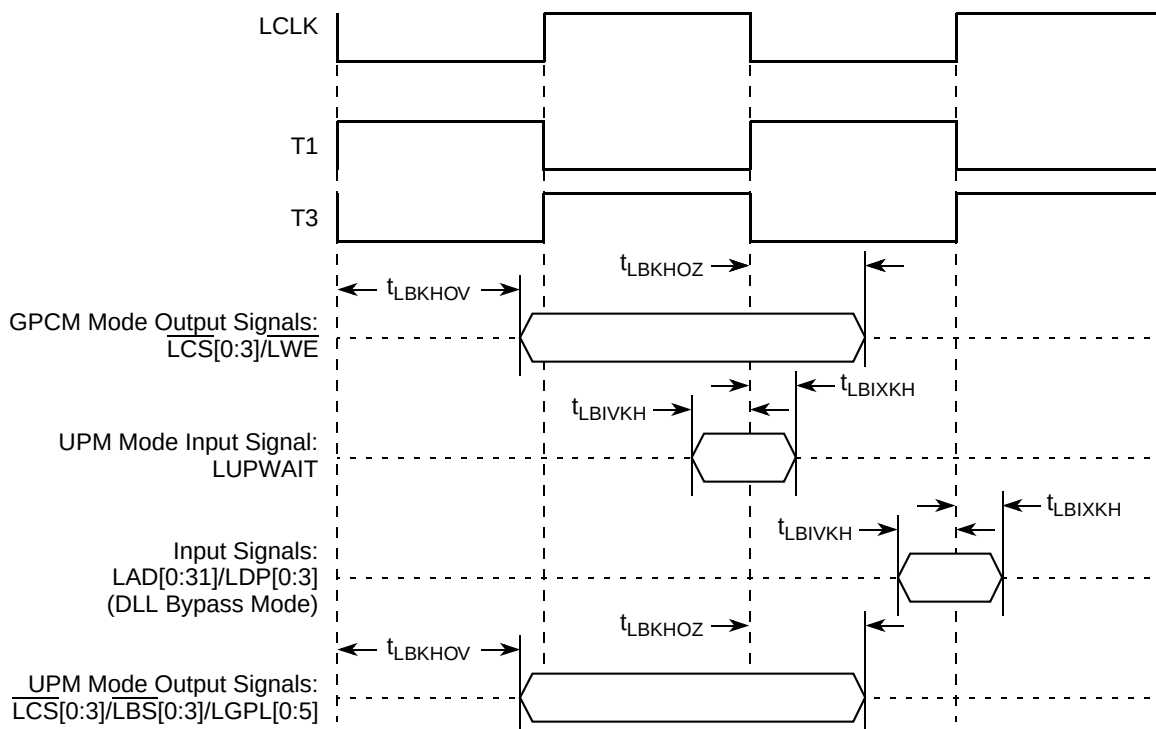


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Bypass Mode)

10.2 JTAG AC Electrical Characteristics

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 33.

Table 43. JTAG AC Timing Specifications (Independent of CLKIN)¹

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock duty cycle	t_{JKHKL}/t_{JTG}	45	55	%	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	—
$\overline{TRST}$ assert time	t_{TRST}	25	—	ns	3
Input setup times:				ns	4
Boundary-scan data TMS, TDI	t_{JTDVKH} t_{JTIVKH}	4 4	— —		
Input hold times:				ns	4
Boundary-scan data TMS, TDI	t_{JTDXKH} t_{JTIXKH}	10 10	— —		
Valid times:				ns	5
Boundary-scan data TDO	t_{JTKLDV} t_{JTKLOV}	2 2	11 11		
Output hold times:				ns	5
Boundary-scan data TDO	t_{JTKLDX} t_{JTKLOX}	2 2	— —		
JTAG external clock to output high impedance:				ns	5, 6
Boundary-scan data TDO	t_{JTKLDZ} t_{JTKLOZ}	2 2	19 9		

Notes:

- All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 22). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
- The symbols used for timing specifications herein follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)}$ (reference)(state) for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- $\overline{TRST}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
- Non-JTAG signal input timing with respect to t_{TCLK} .
- Non-JTAG signal output timing with respect to t_{TCLK} .
- Guaranteed by design and characterization.

JTAG AC Electrical Characteristics

This figure provides the AC test load for TDO and the boundary-scan outputs of the device.

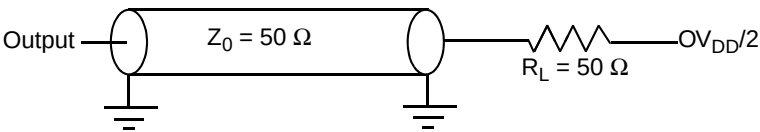


Figure 29. AC Test Load for the JTAG Interface

This figure provides the JTAG clock input timing diagram.

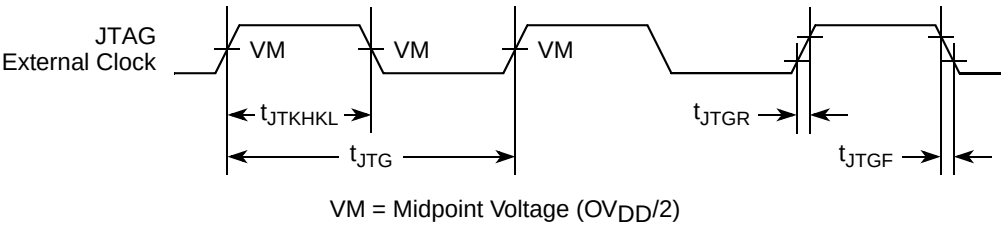


Figure 30. JTAG Clock Input Timing Diagram

This figure provides the $\overline{TRST}$ timing diagram.

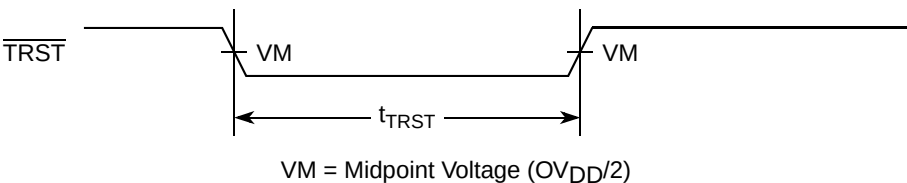


Figure 31. $\overline{TRST}$ Timing Diagram

This figure provides the boundary-scan timing diagram.

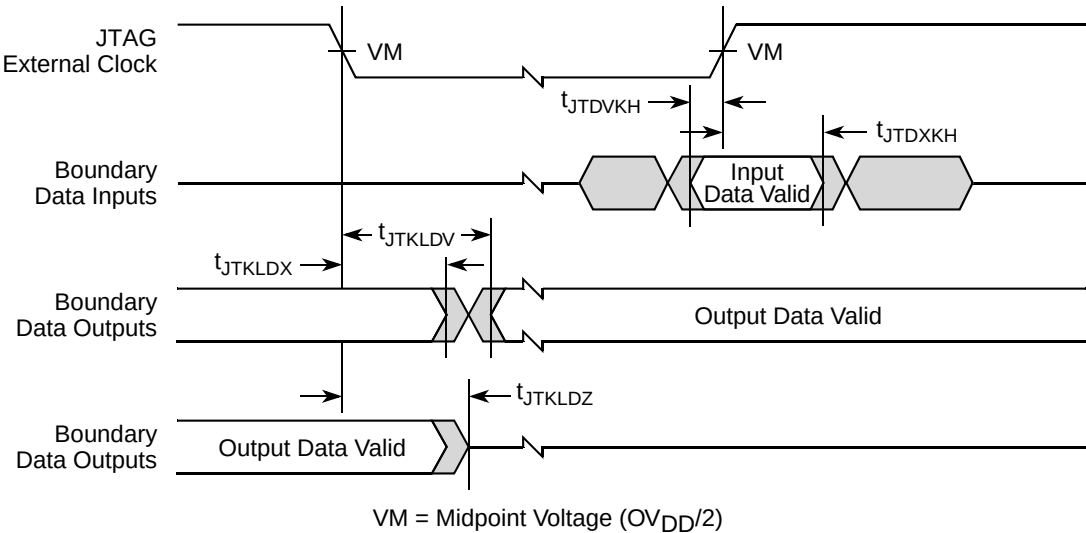
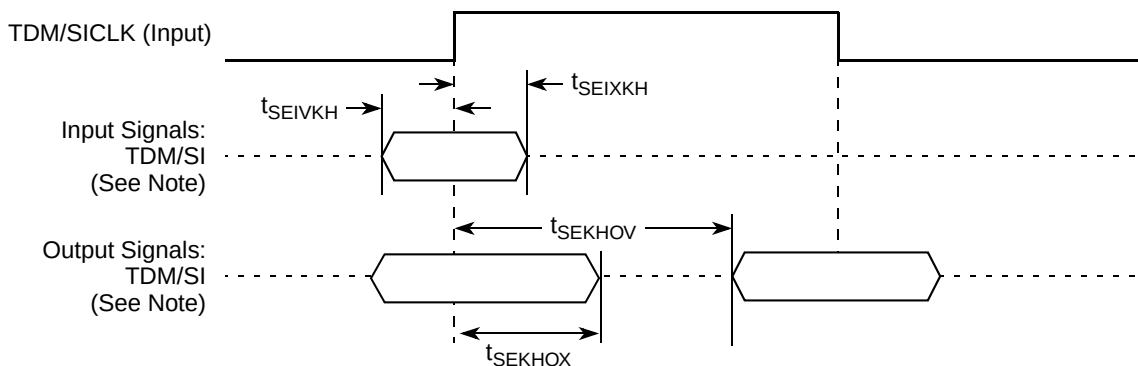


Figure 32. Boundary-Scan Timing Diagram

This figure shows the TDM/SI timing with external clock.



Note: The clock edge is selectable on TDM/SI

Figure 45. TDM/SI AC Timing (External Clock) Diagram

17.3 UTOPIA/POS

This section describes the DC and AC electrical specifications for the UTOPIA/POS of the MPC8360E/58E.

17.4 UTOPIA/POS DC Electrical Characteristics

This table provides the DC electrical characteristics for the device UTOPIA.

Table 59. UTOPIA DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 10	μA

17.5 UTOPIA/POS AC Timing Specifications

This table provides the UTOPIA input and output AC timing specifications.

Table 60. UTOPIA AC Timing Specifications¹

Characteristic	Symbol ²	Min	Max	Unit	Notes
UTOPIA outputs—Internal clock delay	t_{UIKHOV}	0	11.5	ns	—
UTOPIA outputs—External clock delay	t_{UEKHOV}	1	11.6	ns	—
UTOPIA outputs—Internal clock high impedance	t_{UIKHOX}	0	8.0	ns	—
UTOPIA outputs—External clock high impedance	t_{UEKHOX}	1	10.0	ns	—
UTOPIA inputs—Internal clock input setup time	t_{UIIVKH}	6	—	ns	—
UTOPIA inputs—External clock input setup time	t_{UEIVKH}	4	—	ns	3

Table 62. HDLC, BISYNC, and Transparent AC Timing Specifications¹ (continued)

Characteristic	Symbol ²	Min	Max	Unit
Outputs—Internal clock high impedance	t_{HIKHOX}	-0.5	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	8.5	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	1.4	—	ns
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns

Notes:

- Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Table 63. Synchronous UART AC Timing Specifications¹

Characteristic	Symbol ²	Min	Max	Unit
Outputs—Internal clock delay	$t_{UAIKHOV}$	0	11.3	ns
Outputs—External clock delay	$t_{UAEKHOV}$	1	14	ns
Outputs—Internal clock high impedance	$t_{UAIKHOX}$	0	11	ns
Outputs—External clock high impedance	$t_{UAEKHOX}$	1	14	ns
Inputs—Internal clock input setup time	$t_{UAIIVKH}$	6	—	ns
Inputs—External clock input setup time	$t_{UAEIVKH}$	8	—	ns
Inputs—Internal clock input hold time	$t_{UAIIXKH}$	1	—	ns
Inputs—External clock input hold time	$t_{UAEIXKH}$	1	—	ns

Notes:

- Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

This figure provides the AC test load.

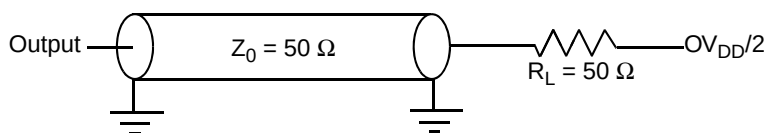


Figure 49. AC Test Load

18.3 AC Test Load

These figures represent the AC timing from [Table 62](#) and [Table 63](#). Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

This figure shows the timing with external clock.

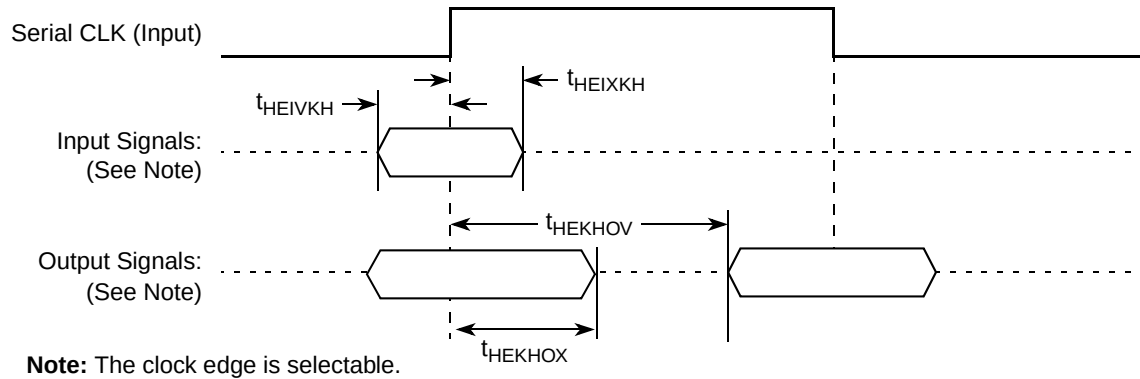


Figure 50. AC Timing (External Clock) Diagram

This figure shows the timing with internal clock.

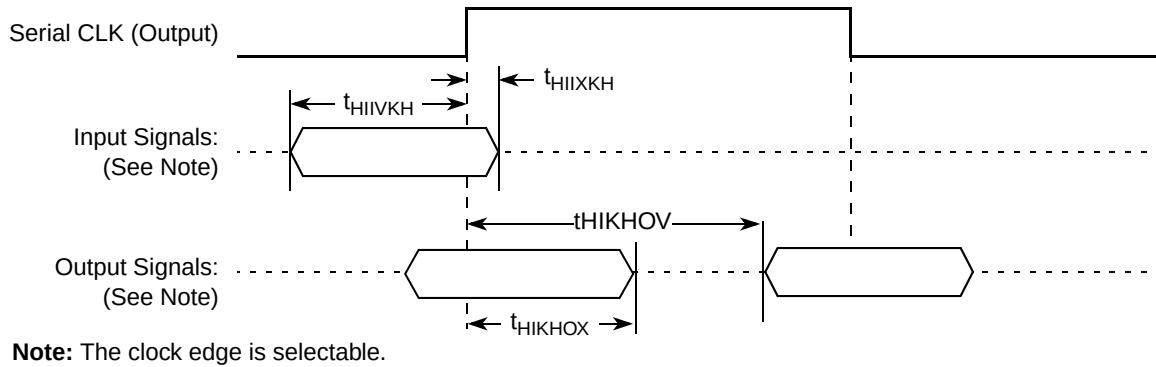


Figure 51. AC Timing (Internal Clock) Diagram

20 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8360E/58E is available in a tape ball grid array (TBGA), see [Section 20.1, “Package Parameters for the TBGA Package,”](#) and [Section 20.2, “Mechanical Dimensions of the TBGA Package,”](#) for information on the package.

20.1 Package Parameters for the TBGA Package

The package parameters for rev. 2.0 silicon are as provided in the following list. The package type is 37.5 mm × 37.5 mm, 740 tape ball grid array (TBGA).

Package outline	37.5 mm × 37.5 mm
Interconnects	740
Pitch	1.00 mm
Module height (typical)	1.46 mm
Solder Balls	62 Sn/36 Pb/2 Ag (ZU package) 95.5 Sn/0.5 Cu/4Ag (VV package)
Ball diameter (typical)	0.64 mm

20.3 Pinout Listings

Refer to AN3097, “MPC8360/MPC8358E PowerQUICC Design Checklist,” for proper pin termination and usage.

This table shows the pin list of the MPC8360E TBGA package.

Table 66. MPC8360E TBGA Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Primary DDR SDRAM Memory Controller Interface				
MEMC1_MDQ[0:31]	AJ34, AK33, AL33, AL35, AJ33, AK34, AK32, AM36, AN37, AN35, AR34, AT34, AP37, AP36, AR36, AT35, AP34, AR32, AP32, AM31, AN33, AM34, AM33, AM30, AP31, AM27, AR30, AT32, AN29, AP29, AN27, AR29	I/O	GV _{DD}	—
MEMC1_MDQ[32:63]/ MEMC2_MDQ[0:31]	AN8, AN7, AM8, AM6, AP9, AN9, AT7, AP7, AU6, AP6, AR4, AR3, AT6, AT5, AR5, AT3, AP4, AM5, AP3, AN3, AN5, AL5, AN4, AM2, AL2, AH5, AK3, AJ2, AJ3, AH4, AK4, AH3	I/O	GV _{DD}	—
MEMC1_MECC[0:4]/ MSRCID[0:4]	AP24, AN22, AM19, AN19, AM24	I/O	GV _{DD}	—
MEMC1_MECC[5]/ MDVAL	AM23	I/O	GV _{DD}	—
MEMC1_MECC[6:7]	AM22, AN18	I/O	GV _{DD}	—
MEMC1_MDM[0:3]	AL36, AN34, AP33, AN28	O	GV _{DD}	—
MEMC1_MDM[4:7]/ MEMC2_MDM[0:3]	AT9, AU4, AM3, AJ6	O	GV _{DD}	—
MEMC1_MDM[8]	AP27	O	GV _{DD}	—
MEMC1_MDQS[0:3]	AK35, AP35, AN31, AM26	I/O	GV _{DD}	—
MEMC1_MDQS[4:7]/ MEMC2_MDQS[0:3]	AT8, AU3, AL4, AJ5	I/O	GV _{DD}	—
MEMC1_MDQS[8]	AP26	I/O	GV _{DD}	—
MEMC1_MBA[0:1]	AU29, AU30	O	GV _{DD}	—
MEMC1_MBA[2]	AT30	O	GV _{DD}	—
MEMC1_MA[0:14]	AU21, AP22, AP21, AT21, AU25, AU26, AT23, AR26, AU24, AR23, AR28, AU23, AR22, AU20, AR18	O	GV _{DD}	—
MEMC1_MODT[0:1]	AG33, AJ36	O	GV _{DD}	6
MEMC1_MODT[2:3]/ MEMC2_MODT[0:1]	AT1, AK2	O	GV _{DD}	6
MEMC1_MWE	AT26	O	GV _{DD}	—
MEMC1_MRAS	AT29	O	GV _{DD}	—
MEMC1_MCAS	AT24	O	GV _{DD}	—
MEMC1_MCS[0:1]	AU27, AT27	O	GV _{DD}	—
MEMC1_MCS[2:3]/ MEMC2_MCS[0:1]	AU8, AU7	O	GV _{DD}	—

Table 66. MPC8360E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PMC				
$\overline{\text{QUIESCE}}$	B36	O	OV_{DD}	—
System Control				
$\overline{\text{PORESET}}$	L37	I	OV_{DD}	—
$\overline{\text{HRESET}}$	L36	I/O	OV_{DD}	1
$\overline{\text{SRESET}}$	M33	I/O	OV_{DD}	2
Thermal Management				
THERM0	AP19	I	GV_{DD}	—
THERM1	AT31	I	GV_{DD}	—
Power and Ground Signals				
$\text{AV}_{\text{DD}1}$	K35	Power for LBIU DLL (1.2 V)	$\text{AV}_{\text{DD}1}$	—
$\text{AV}_{\text{DD}2}$	K36	Power for CE PLL (1.2 V)	$\text{AV}_{\text{DD}2}$	—
$\text{AV}_{\text{DD}5}$	AM29	Power for e300 PLL (1.2 V)	$\text{AV}_{\text{DD}5}$	—
$\text{AV}_{\text{DD}6}$	K37	Power for system PLL (1.2 V)	$\text{AV}_{\text{DD}6}$	—
GND	A2, A8, A13, A19, A22, A25, A31, A33, A36, B7, B12, B24, B27, B30, C4, C6, C9, C15, C26, C32, D3, D8, D11, D14, D17, D19, D23, D27, E7, E13, E25, E30, E36, F4, F37, G34, H1, H5, H32, H33, J4, J32, J37, K1, L3, L5, L33, L34, M1, M34, M35, N37, P2, P5, P35, P36, R4, T3, U1, U5, U35, V37, W1, W4, W33, W36, Y34, AA3, AA5, AC3, AC32, AC35, AD1, AD37, AE4, AE34, AE36, AF33, AG4, AG6, AG32, AH35, AJ1, AJ4, AJ32, AJ35, AJ37, AK36, AL3, AL34, AM4, AN6, AN23, AN30, AP8, AP12, AP14, AP16, AP17, AP20, AP25, AR6, AR8, AR9, AR19, AR24, AR31, AR35, AR37, AT4, AT10, AT19, AT20, AT25, AU14, AU22, AU28, AU35	—	—	—
GV_{DD}	AD4, AE3, AF1, AF5, AF35, AF37, AG2, AG36, AH33, AH34, AK5, AM1, AM35, AM37, AN2, AN10, AN11, AN12, AN14, AN32, AN36, AP5, AP23, AP28, AR1, AR7, AR10, AR12, AR21, AR25, AR27, AR33, AT15, AT22, AT28, AT33, AU2, AU5, AU16, AU31, AU36	Power for DDR DRAM I/O voltage (2.5 or 1.8 V)	GV_{DD}	—

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI_MODE	D36	I	OV _{DD}	—
M66EN/CE_PF[4]	B37	I/O	OV _{DD}	—
Local Bus Controller Interface				
LAD[0:31]	N32, N33, N35, N36, P37, P32, P34, R36, R35, R34, R33, T37, T35, T34, T33, U37, T32, U36, U34, V36, V35, W37, W35, V33, V32, W34, Y36, W32, AA37, Y33, AA35, AA34	I/O	OV _{DD}	—
LDP[0]/CKSTOP_OUT	AB37	I/O	OV _{DD}	—
LDP[1]/CKSTOP_IN	AB36	I/O	OV _{DD}	—
LDP[2]/LCS[6]	AB35	I/O	OV _{DD}	—
LDP[3]/LCS[7]	AA33	I/O	OV _{DD}	—
LA[27:31]	AC37, AA32, AC36, AC34, AD36	O	OV _{DD}	—
LCS[0:5]	AD33, AG37, AF34, AE33, AD32, AH37	O	OV _{DD}	—
LWE[0:3]/LSDDQM[0:3]/LBS[0:3]	AG35, AG34, AH36, AE32	O	OV _{DD}	—
LBCTL	AD35	O	OV _{DD}	—
LALE	M37	O	OV _{DD}	—
LGPL0/LSDA10/cfg_reset_source0	AB32	I/O	OV _{DD}	—
LGPL1/LSDWE/cfg_reset_source1	AE37	I/O	OV _{DD}	—
LGPL2/LSDRAS/LOE	AC33	O	OV _{DD}	—
LGPL3/LSDCAS/cfg_reset_source2	AD34	I/O	OV _{DD}	—
LGPL4/LGTA/LUPWAIT/LPBSE	AE35	I/O	OV _{DD}	—
LGPL5/cfg_clkin_div	AF36	I/O	OV _{DD}	—
LCKE	G36	O	OV _{DD}	—
LCLK[0]	J33	O	OV _{DD}	—
LCLK[1]/LCS[6]	J34	O	OV _{DD}	—
LCLK[2]/LCS[7]	G37	O	OV _{DD}	—
LSYNC_OUT	F34	O	OV _{DD}	—
LSYNC_IN	G35	I	OV _{DD}	—
Programmable Interrupt Controller				
MCP_OUT	E34	O	OV _{DD}	2
IRQ0/MCP_IN	C37	I	OV _{DD}	—
IRQ[1]/M1SRCID[4]/M2SRCID[4]/LSRCID[4]	F35	I/O	OV _{DD}	—
IRQ[2]/M1DVAL/M2DVAL/LDVAL	F36	I/O	OV _{DD}	—
IRQ[3]/CORE_SRESET	H34	I/O	OV _{DD}	—

Table 76. Suggested PLL Configurations (continued)

Conf No. ¹	SPMF	CORE PLL	CEPMF	CEPDF	Input Clock Freq (MHz)	CSB Freq (MHz)	Core Freq (MHz)	QUICC Engine Freq (MHz)	400 (MHz)	533 (MHz)	667 (MHz)
c5	æ	æ	10000	0	33	—	—	533	—	∞	∞
c6	æ	æ	10001	0	33	—	—	566	—	—	∞
66 MHz CLKIN/PCI_SYNC_IN Options											
s1h	0011	0000110	æ	æ	66	200	400	—	∞	∞	∞
s2h	0011	0000101	æ	æ	66	200	500	—	—	∞	∞
s3h	0011	0000110	æ	æ	66	200	600	—	—	—	∞
s4h	0100	0000011	æ	æ	66	266	400	—	∞	∞	∞
s5h	0100	0000100	æ	æ	66	266	533	—	—	∞	∞
s6h	0100	0000101	æ	æ	66	266	667	—	—	—	∞
s7h	0101	0000010	æ	æ	66	333	333	—	∞	∞	∞
s8h	0101	0000011	æ	æ	66	333	500	—	—	∞	∞
s9h	0101	0000100	æ	æ	66	333	667	—	—	—	∞
c1h	æ	æ	00101	0	66	—	—	333	∞	∞	∞
c2h	æ	æ	00110	0	66	—	—	400	∞	∞	∞
c3h	æ	æ	00111	0	66	—	—	466	—	∞	∞
c4h	æ	æ	01000	0	66	—	—	533	—	∞	∞
c5h	æ	æ	01001	0	66	—	—	600	—	—	∞

Note:

1. The Conf No. consist of prefix, an index and a postfix. The prefix “s” and “c” stands for “sysset” and “ce” respectively. The postfix “h” stands for “high input clock.”The index is a serial number.

The following steps describe how to use above table. See [Example 1](#).

2. Choose the up or down sections in the table according to input clock rate 33 MHz or 66 MHz.
3. Select a suitable CSB and core clock rates from [Table 76](#). Copy the SPMF and CORE PLL configuration bits.
4. Select a suitable QUICC Engine block clock rate from [Table 76](#). Copy the CEPMPF and CEPDF configuration bits.
5. Insert the chosen SPMF, COREPLL, CEPMPF and CEPDF to the RCWL fields, respectively.

23.7 Pull-Up Resistor Requirements

The device requires high resistance pull-up resistors (10 k Ω is recommended) on open drain type pins including I²C pins, Ethernet Management MDIO pin, and EPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, see *MPC8360E/MPC8358E PowerQUICC Design Checklist* (AN3097).

24 Ordering Information

24.1 Part Numbers Fully Addressed by this Document

This table provides the Freescale part numbering nomenclature for the MPC8360E/58E. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. Additionally to the processor frequency, the part numbering scheme also includes an application modifier, which may specify special application conditions. Each part number also contains a revision code that refers to the die mask revision number.

Table 80. Part Numbering Nomenclature¹

<i>MPC</i>	<i>nnnn</i>	<i>e</i>	<i>t</i>	<i>pp</i>	<i>aa</i>	<i>a</i>	<i>a</i>	<i>A</i>
Product Code	Part Identifier	Encryption Acceleration	Temperature Range	Package ²	Processor Frequency ³	Platform Frequency	QUICC Engine Frequency	Die Revision
MPC	8358	Blank = not included E = included	Blank = 0° C T _A to 105° C T _J C= -40° C T _A to 105° C T _J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AD = 266 MHz AG = 400 MHz	D = 266 MHz	E = 300 MHz G = 400 MHz	A = rev. 2.1 silicon
	8360				e300 core speed AG = 400 MHz AJ = 533 MHz AL = 667 MHz	D = 266 MHz F = 333 MHz	G = 400 MHz H = 500 MHz	A = rev. 2.1 silicon
MPC (rev. 2.0 silicon only)	8360	Blank = not included E = included	0° C T _A to 70° C T _J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AH = 500 MHz AL = 667 MHz	F = 333 MHz	G = 400 MHz H = 500 MHz	—

Notes:

- Not all processor, platform, and QUICC Engine block frequency combinations are supported. For available frequency combinations, contact your local Freescale sales office or authorized distributor.
- See [Section 20, "Package and Pin Listings,"](#) for more information on available package types.
- Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.

This table shows the SVR settings by device and package type.

Table 81. SVR Settings

Device	Package	SVR (Rev. 2.0)	SVR (Rev. 2.1)
MPC8360E	TBGA	0x8048_0020	0x8048_0021
MPC8360	TBGA	0x8049_0020	0x8049_0021